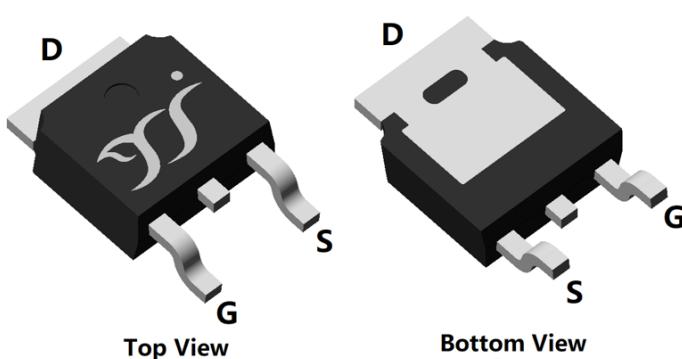
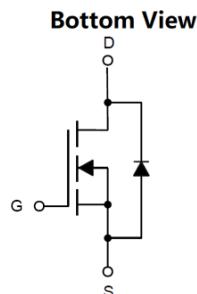




N-Channel Enhancement Mode Field Effect Transistor



TO-252



Product Summary

- V_{DS} 40 V
- I_D 60 A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) <7.0 mohm
- $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) <9.5 mohm
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- High current load applications
- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | | Symbol | Limit | Unit |
|--|-------------------------|-----------------|----------|---------------------------|
| Drain-source Voltage | | V_{DS} | 40 | V |
| Gate-source Voltage | | V_{GS} | ± 20 | V |
| Drain Current | $T_c=25^\circ\text{C}$ | I_D | 60 | A |
| | $T_c=100^\circ\text{C}$ | | 38 | |
| Pulsed Drain Current ^A | | I_{DM} | 200 | A |
| Total Power Dissipation | $T_c=25^\circ\text{C}$ | P_D | 44 | W |
| | $T_c=100^\circ\text{C}$ | | 17 | |
| Single Pulse Avalanche Energy ^B | | E_{AS} | 110 | mJ |
| Thermal Resistance Junction-to-Case ^C | | $R_{\theta JC}$ | 2.8 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | | T_J, T_{STG} | -55~+150 | $^\circ\text{C}$ |

■ Ordering Information (Example)

| PREFERRED P/N | PACKING CODE | Marking | MINIMUM PACKAGE(pcs) | INNER BOX QUANTITY(pcs) | OUTER CARTON QUANTITY(pcs) | DELIVERY MODE |
|---------------|--------------|-----------|----------------------|-------------------------|----------------------------|---------------|
| YJD60N04A | F1/F2 | YJD60N04A | 2500 | / | 25000 | 13" reel |



YJD60N04A

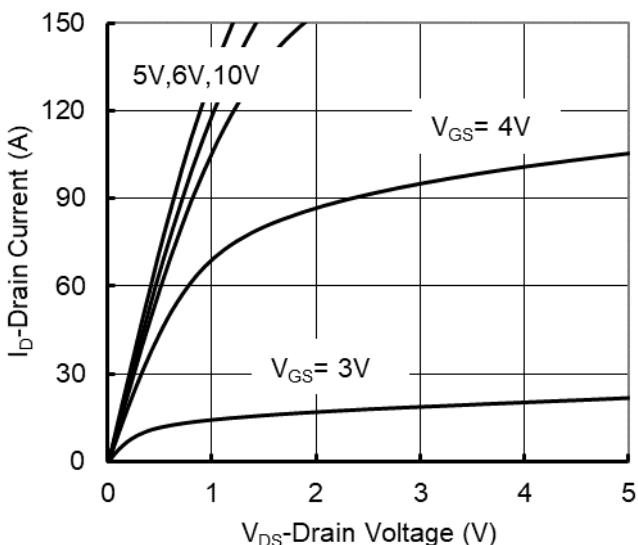
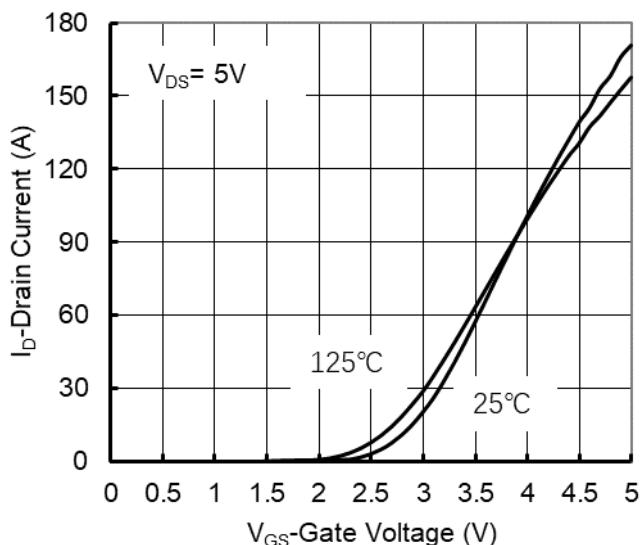
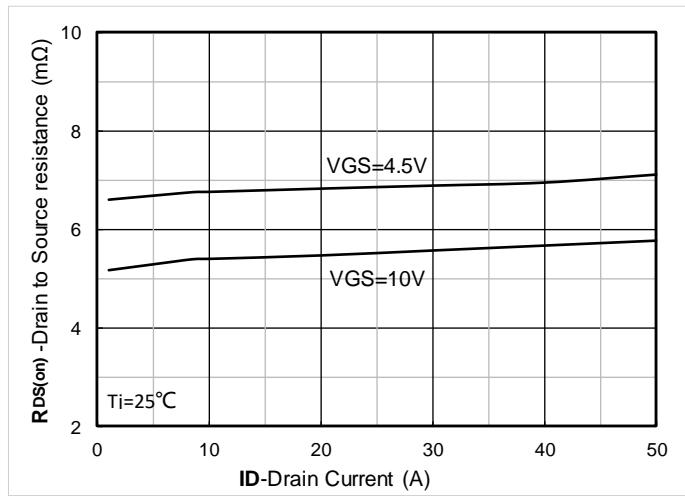
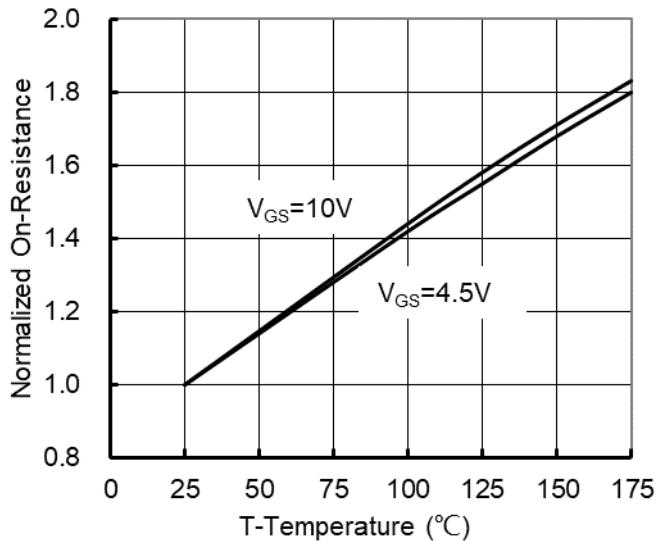
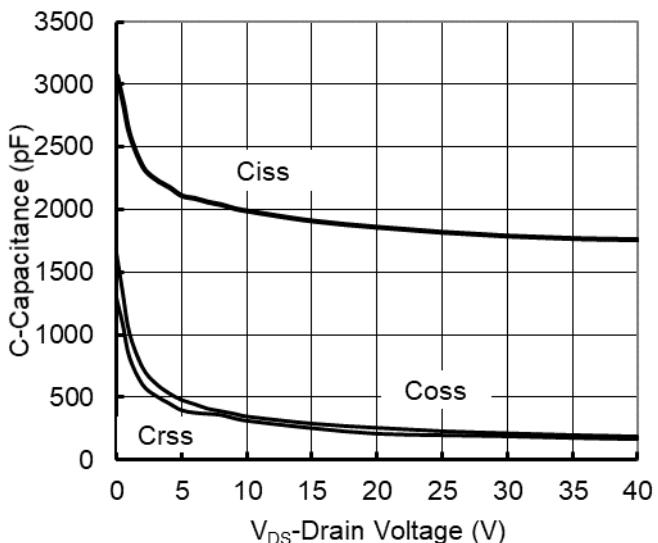
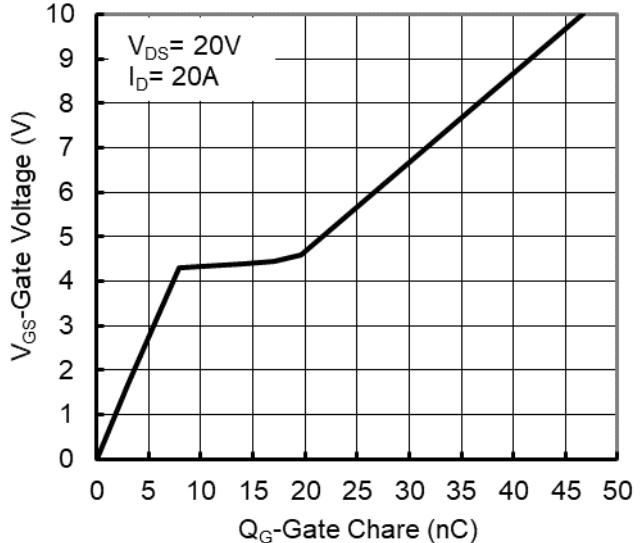
■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Conditions | | Min | Typ | Max | Units |
|---------------------------------------|--------------------------|--|-------------------------|-----|------|-----------|------------------|
| Static Parameter | | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$ | | 40 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{\text{DS}}=40\text{V}, V_{\text{GS}}=0\text{V}$ | $T_J=25^\circ\text{C}$ | | | 1 | μA |
| | | | $T_J=150^\circ\text{C}$ | | | 100 | |
| Gate-Body Leakage Current | I_{GSS} | $V_{\text{GS}}= \pm 20\text{V}, V_{\text{DS}}=0\text{V}$ | | | | ± 100 | nA |
| Gate Threshold Voltage | $V_{\text{GS(th)}}$ | $V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$ | | 1.0 | 1.5 | 2.5 | V |
| Static Drain-Source On-Resistance | $R_{\text{DS(ON)}}$ | $V_{\text{GS}}= 10\text{V}, I_{\text{D}}=20\text{A}$ | | | 5.4 | 7 | $\text{m}\Omega$ |
| | | $V_{\text{GS}}= 4.5\text{V}, I_{\text{D}}=10\text{A}$ | | | 6.8 | 9.5 | |
| Diode Forward Voltage | V_{SD} | $I_{\text{S}}=20\text{A}, V_{\text{GS}}=0\text{V}$ | | | 0.8 | 1.2 | V |
| Maximum Body-Diode Continuous Current | I_{S} | | | | | 60 | A |
| Dynamic Parameters | | | | | | | |
| Input Capacitance | C_{iss} | $V_{\text{DS}}=20\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$ | | | 1860 | | pF |
| Output Capacitance | C_{oss} | | | | 256 | | |
| Reverse Transfer Capacitance | C_{rss} | | | | 205 | | |
| Switching Parameters | | | | | | | |
| Total Gate Charge | Q_{g} | $V_{\text{GS}}=10\text{V}, V_{\text{DS}}=20\text{V}, I_{\text{D}}=20\text{A}$ | | | 46.7 | | nC |
| Gate-Source Charge | Q_{gs} | | | | 8 | | |
| Gate-Drain Charge | Q_{gd} | | | | 11.6 | | |
| Reverse Recovery Charge | Q_{rr} | $I_{\text{F}}=20\text{A}, dI/dt=100\text{A/us}$ | | | 2.3 | | ns |
| Reverse Recovery Time | t_{rr} | | | | 15 | | |
| Turn-on Delay Time | $t_{\text{D(on)}}$ | | | | 10 | | |
| Turn-on Rise Time | t_{r} | $V_{\text{GS}}=10\text{V}, V_{\text{DD}}=20\text{V}, I_{\text{D}}=2\text{A}, R_{\text{L}}=1\Omega, R_{\text{GEN}}=3\Omega$ | | | 21 | | ns |
| Turn-off Delay Time | $t_{\text{D(off)}}$ | | | | 36 | | |
| Turn-off fall Time | t_{f} | | | | 25 | | |

A. Pulse Test: Pulse Width $\leq 300\text{us}$, Duty cycle $\leq 2\%$.

B. $T_J=25^\circ\text{C}$, $V_{\text{DD}}=38\text{V}$, $V_G=10\text{V}$, $L=0.5\text{mH}$, $I_{\text{AS}}=21\text{A}$

C. R_{\thetaJA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{\thetaJC} is guaranteed by design, while R_{\thetaJA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.

**■ Typical Performance Characteristics****Figure 1. Output Characteristics****Figure 2. Transfer Characteristics****Figure 3. On-Resistance vs. Drain Current and Gate Voltage****Figure 4. On-Resistance vs. Junction Temperature****Figure 5. Capacitance Characteristics****Figure 6. Gate Charge**



YJD60N04A

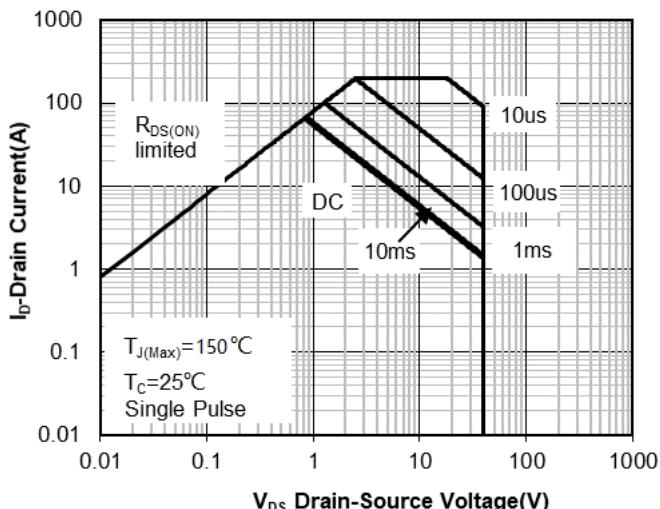


Figure 7. Safe Operation Area

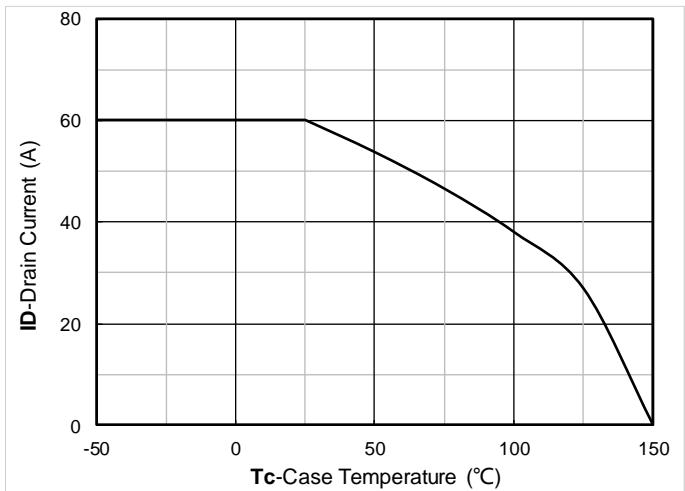


Figure 8. Maximum Continuous Drain Current vs Case Temperature

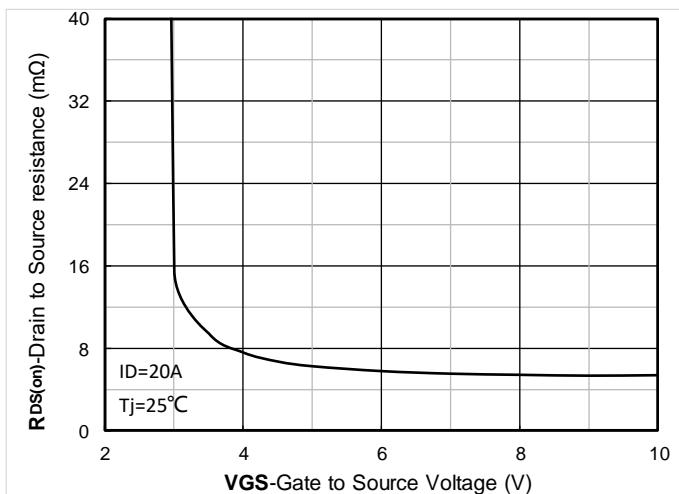


Figure 9. On-Resistance vs Gate to Source Voltage

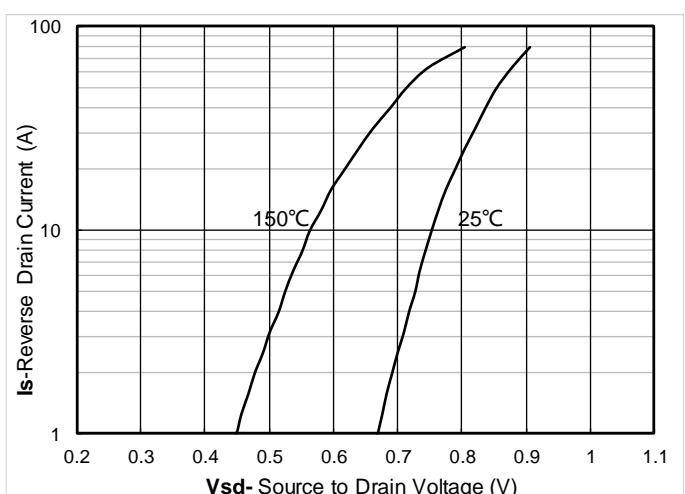


Figure 10. Forward characteristics of reverse diode

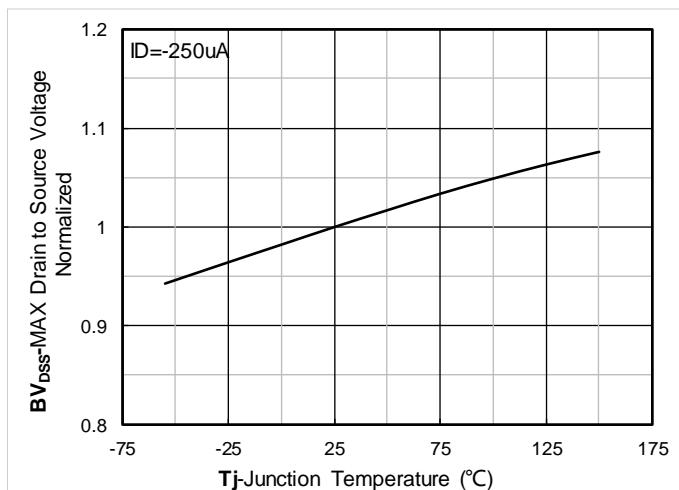


Figure 11. Normalized breakdown voltage

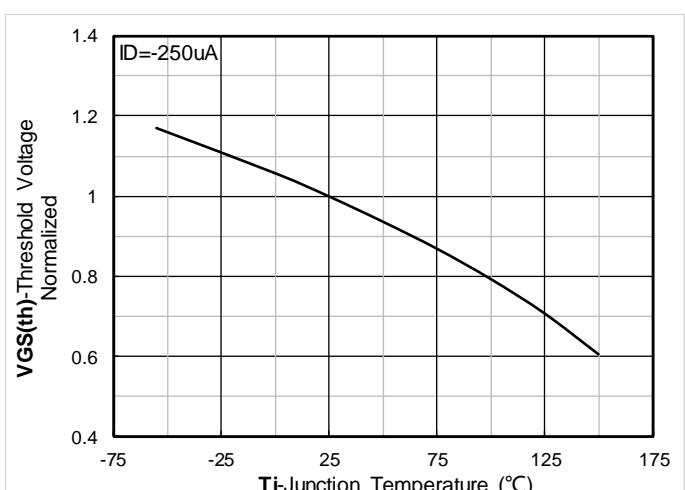


Figure 12. Normalized Threshold voltage

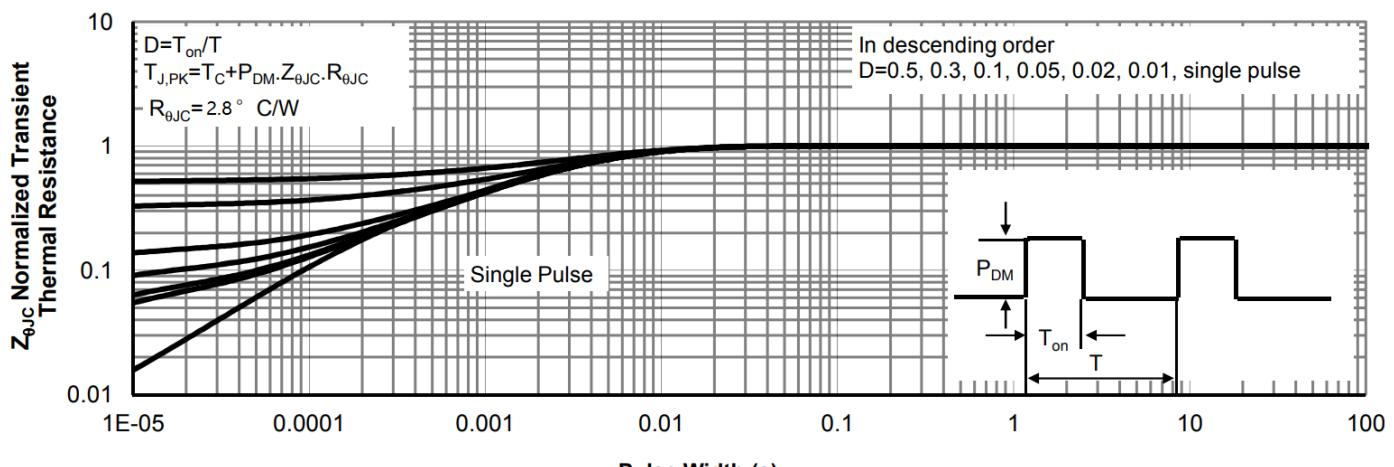
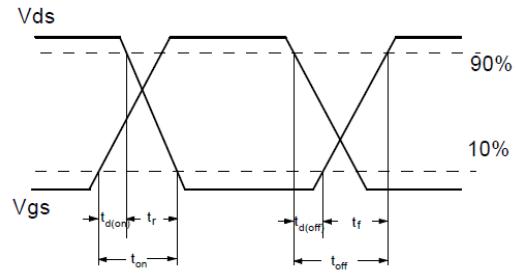
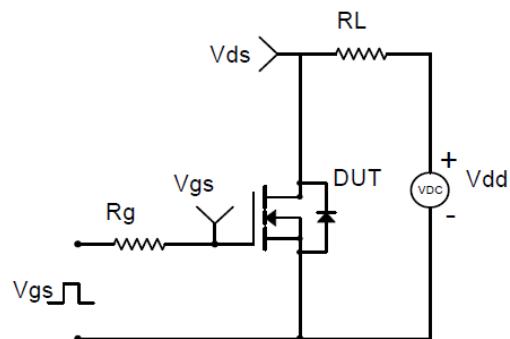
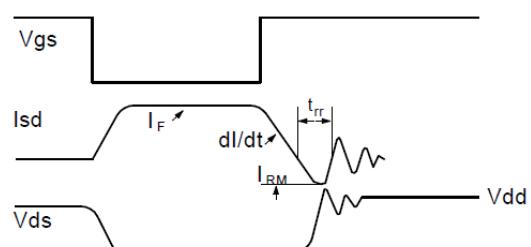
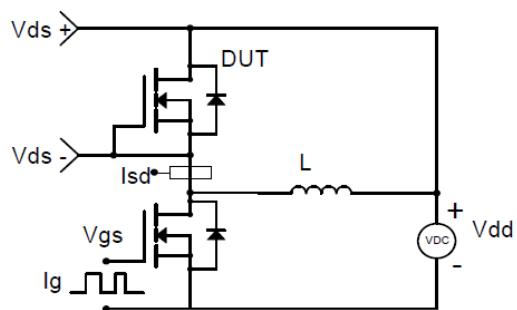


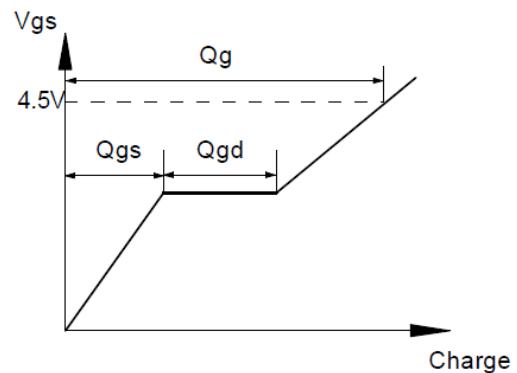
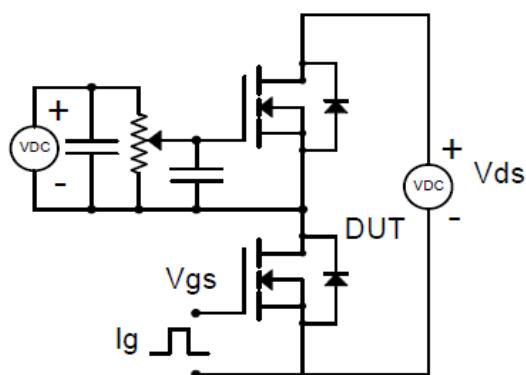
Figure 13. Normalized Maximum Transient Thermal Impedance



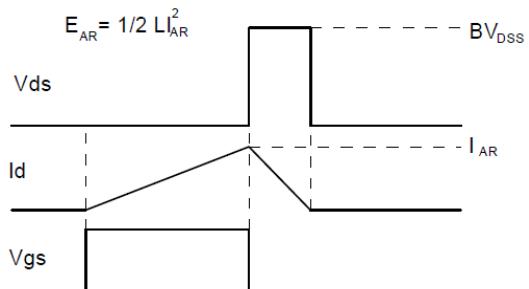
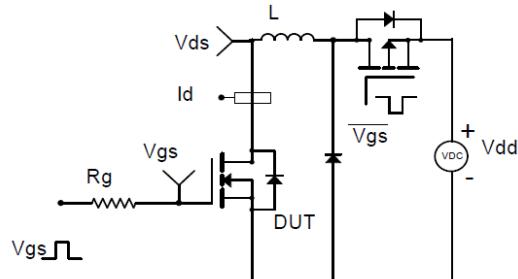
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



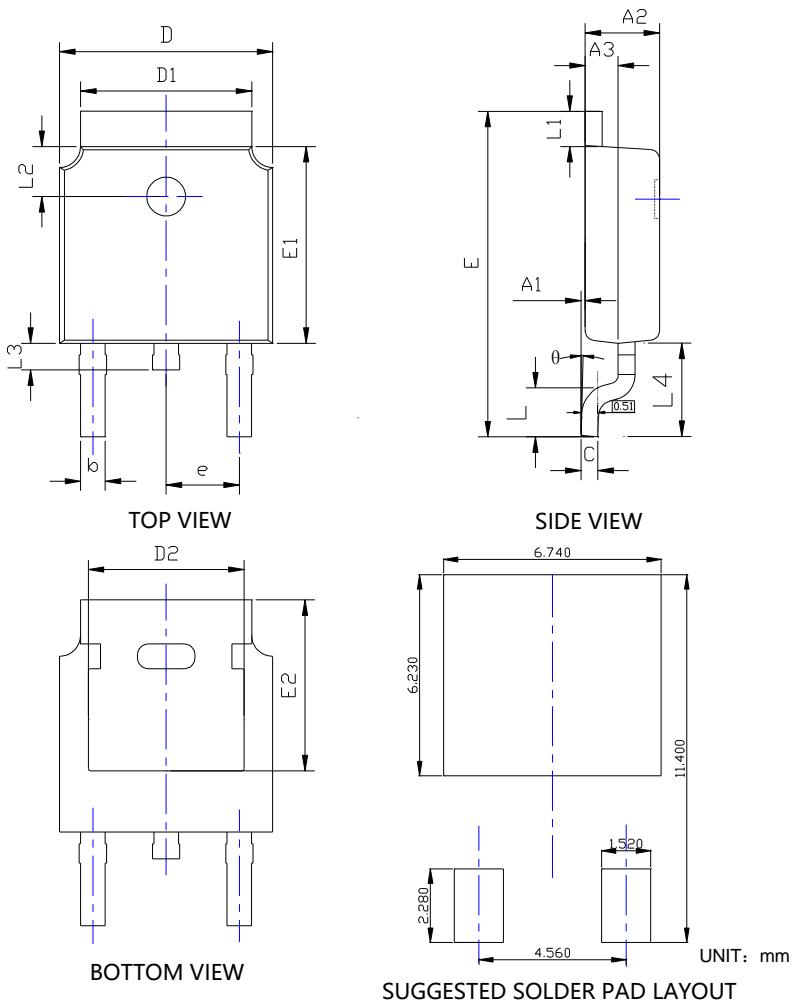
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



■ TO-252-B Package information



| SYMBOL | INCHES | | | Millimeter | | |
|--------|----------|-------|-------|------------|--------|--------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A1 | 0.000 | --- | 0.008 | 0.000 | --- | 0.200 |
| A2 | 0.087 | 0.091 | 0.094 | 2.200 | 2.300 | 2.400 |
| A3 | 0.035 | 0.039 | 0.043 | 0.900 | 1.000 | 1.100 |
| b | 0.026 | 0.030 | 0.034 | 0.660 | 0.760 | 0.860 |
| c | 0.018 | 0.020 | 0.023 | 0.460 | 0.520 | 0.580 |
| D | 0.256 | 0.260 | 0.264 | 6.500 | 6.600 | 6.700 |
| D1 | 0.203 | 0.209 | 0.215 | 5.150 | 5.300 | 5.450 |
| D2 | 0.181 | 0.189 | 0.195 | 4.600 | 4.800 | 4.950 |
| E | 0.390 | 0.398 | 0.406 | 9.900 | 10.100 | 10.300 |
| E1 | 0.236 | 0.240 | 0.244 | 6.000 | 6.100 | 6.200 |
| E2 | 0.203 | 0.209 | 0.215 | 5.150 | 5.300 | 5.450 |
| e | 0.090BSC | | | 2.286BSC | | |
| L | 0.049 | 0.059 | 0.069 | 1.250 | 1.500 | 1.750 |
| L1 | 0.035 | --- | 0.050 | 0.900 | --- | 1.270 |
| L2 | 0.055 | --- | 0.075 | 1.400 | --- | 1.900 |
| L3 | 0.240 | 0.310 | 0.039 | 6.000 | 0.800 | 1.000 |
| L4 | 0.114REF | | | 2.900REF | | |
| θ | 0° | --- | 10° | 0° | --- | 10° |

NOTE:

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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